

THYRISTOR MODULE

PK(PD,PE,KK)130F

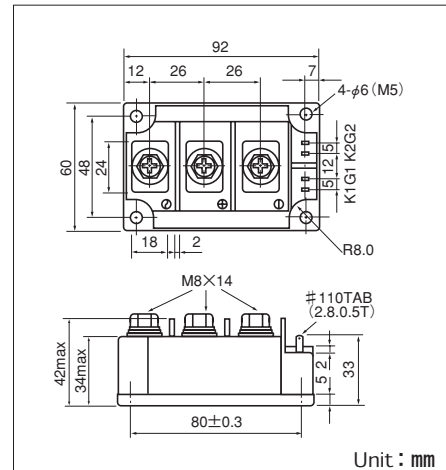
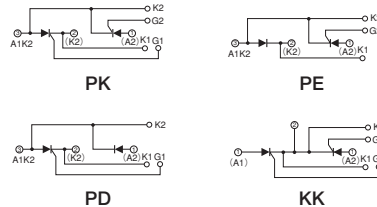
UL:E76102(M)

Power Thyristor/Diode Module **PK130F** series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 1,600V are available. Two elements in a package and electrically isolated mounting base make your mechanical design easy.

- $I_T(AV)$ 130A, $I_T(RMS)$ 205A, I_{TSM} 4400A
- di/dt 200A/ μ s
- dv/dt 500V/ μ s

(Applications)

Various rectifiers
AC/DC motor drives
Heater controls
Light dimmers
Static switches



Unit : mm

Maximum Ratings

Symbol	Item	Ratings				Unit
		PK130F40 PD130F40 PE130F40 KK130F40	PK130F80 PD130F80 PE130F80 KK130F80	PK130F120 PD130F120 PE130F120 KK130F120	PK130F160 PD130F160 PE130F160 KK130F160	
V_{RRM}	* Repetitive Peak Reverse Voltage	400	800	1200	1600	V
V_{RSM}	* Non-Repetitive Peak Reverse Voltage	480	960	1300	1700	V
V_{DRM}	Repetitive Peak Off-State Voltage	400	800	1200	1600	V

Symbol	Item	Conditions	Ratings	Unit	
$I_T(AV)$	* Average On-State Current	Single phase, half wave, 180° conduction, $T_c : 90^\circ C$	130	A	
$I_T(RMS)$	* R.M.S. On-State Current	Single phase, half wave, 180° conduction, $T_c : 90^\circ C$	205	A	
I_{TSM}	* Surge On-State Current	1/2 cycle, 50Hz/60Hz, peak Value, non-repetitive	4000/ 4400	A	
I^2t	* I^2t	Value for one cycle of surge current	8×10^4	A ² S	
P_{GM}	Peak Gate Power Dissipation		10	W	
$P_{G(AV)}$	Average Gate Power Dissipation		3	W	
I_{FGM}	Peak Gate Current		3	A	
V_{FGM}	Peak Gate Voltage (Forward)		10	V	
V_{RGM}	Peak Gate Voltage (Reverse)		5	V	
di/dt	Critical Rate of Rise of On-State Current	$I_G=100mA, T_j=25^\circ C, V_D=1/2 V_{DRM}, di/dt=0.1A/\mu s$	200	A/ μs	
V_{ISO}	* Isolation Breakdown Voltage (R.M.S.)	A.C. 1minute	2500	V	
T_j	* Operating Junction Temperature		- 40 to +125	°C	
T_{stg}	* Storage Temperature		- 40 to +125	°C	
	Mounting Torque	Mounting (M5)	Recommended 1.5-2.5 (15-25)	2.7 (28)	N·m (kgf·cm)
		Terminal (M8)	Recommended 8.8-10 (90-105)	11 (115)	
	Mass		510	g	

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , single phase, half wave, $T_j=125^\circ C$	50	mA
I_{RRM}	* Repetitive Peak Reverse Current, max.	at V_{DRM} , single phase, half wave, $T_j=125^\circ C$	50	mA
V_{TM}	* Peak On-State Voltage, max.	On-State Current 400A, $T_j=25^\circ C$ Inst measurement	1.40	V
I_{GT}/V_{GT}	Gate Trigger Current/Voltage, max.	$T_j=25^\circ C, I_T=1A, V_D=6V$	100/3	mA/V
V_{GD}	Non-Trigger Gate, Voltage, min.	$T_j=125^\circ C, V_D=1/2 V_{DRM}$	0.25	V
t_{gt}	Turn On Time, max.	$I_r=130A, I_g=100mA, T_j=25^\circ C, V_D=1/2 V_{DRM}, di/dt=0.1A/\mu s$	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_j=125^\circ C, V_D=2/3 V_{DRM}$, Exponential wave.	500	V/ μs
I_H	Holding Current, typ.	$T_j=25^\circ C$	50	mA
I_L	Latching Current, typ.	$T_j=25^\circ C$	100	mA
$R_{th(j-c)}$	* Thermal Impedance, max.	Junction to case	0.2	°C/W

* mark : Thyristor and Diode part. No mark : Thyristor part

